





RL201-RL207 1.0 SILICON RECTIFIERS



Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: JEDEC DO-15 molded plastic body
- Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.014 ounce, 0.40 grams

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Type Number	Symbol	RL201	RL202	RL203	RL204	RL205	RL206	RL207	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Average forward rectified output current $@T_A = 75^{\circ}C$	Io				2.0				Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}				70				А
Forward Voltage @I _F =2.0A	V_{FM}				1.0				V
Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 100°C	I _{RM}				5.0 50				μA
Typical Junction Capacitance (Note 1)	CJ				20				pF
Typical Thermal Resistance Junction to Ambient (Note 2)	R _{θJA}				40				°C/W
Operating Junction Temperature Range	TJ			_	65 to +1	25			°C
Storage Temperature Range	T _{STG}			-	65 to +1	50			°C

*Glass passivated forms are available upon request

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

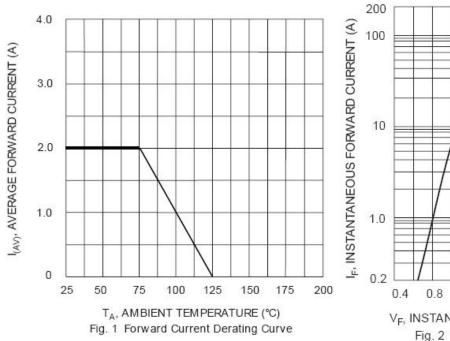
- 2. Thermal resistance from junction to ambient at 0.375"(9.5mm)lead length, P.C.B. mounted
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 sales@ smc-diodes.com

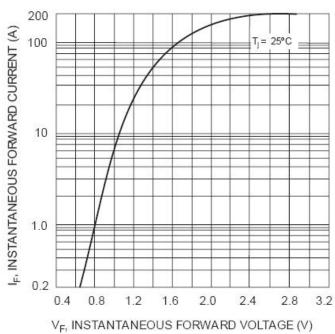




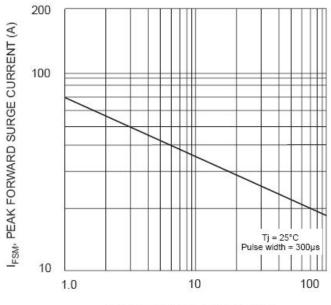


Ratings and Characteristics Curves

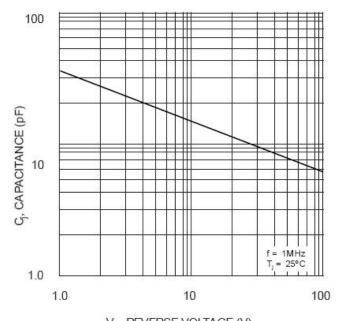




F, INSTANTANEOUS FORWARD VOLTAGE (V) Fig. 2 Typical Forward Characteristics







V_R, REVERSE VOLTAGE (V) Fig. 4 Typical Junction Capacitance

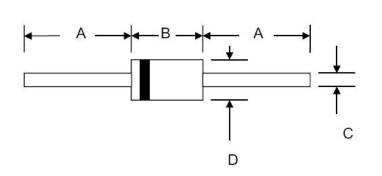
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Mechanical Dimensions DO-15



SYMBOL	Millin	neters	Inches			
OTMBOL	Min.	Max.	Min.	Max.		
А	25.4	-	1.000	-		
В	5.5	7.62	0.217	0.300		
С	0.7	0.9	0.028	0.034		
D	2.6	3.6	0.104	0.140		

Ordering Information

Device	Package	Shipping		
RL201-RL207	DO-15	2000noo /tono		
	(Pb-Free)	3000pcs /tape		

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Where XXXXX is YYWWL

 RL201
 = Type Number

 SSG
 = SSG

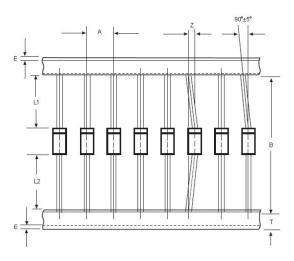
 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

Carrier Tape Specification DO-15



SYMBOL	Millimeters			
	Min.	Max.		
А	4.50	5.50		
В	50.9	53.9		
Z	-	1.20		
Т	5.60	6.40		
E	-	0.80		
IL1-L2I	-	1.0		

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